



TO-92L Plastic-Encapsulate Transistors

KTC3207 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

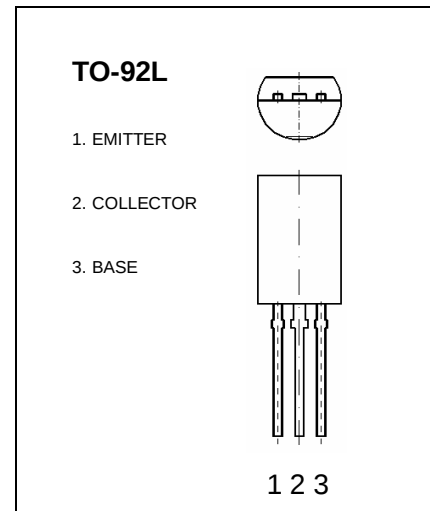
I_{CM} : 100 mA

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=240V, I_E=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			1.0	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=4mA$	20			
	$h_{FE(2)}$	$V_{CE}=10V, I_C=20mA$	30		150	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Transition frequency	f_T	$V_{CE}=10V, I_C=20mA$	50			MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=20V, I_E=0, f=1MHz$		3.0		pF